

Zener Diode Chips (Dual Pad) for ESD Bidirectional Protection

1. Feature:

- 1-1 Silicon Zener diode chips for electrostatic discharge (ESD) protection application
- 1-2 This specification applies to N/P/N-Type silicon Zener diode chip (Dual pad/Vertical)
- Device NO:WT-Z210V-AU4

2. Structure:

- 2-1 Planar type: Silicon Diode
- 2-2 Electrodes:
 - Top side : Gold Pad.(Cathode)
 - Back side : Gold Layer.(Anode)

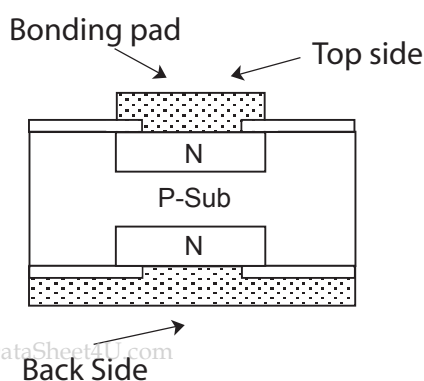
3. Size:

- 3-1 Chip size: 10.0 mils x 10.0 mils (254 μ m x 254 μ m).
- 3-2 Chip thickness: 4.0 $\pm$ 1.0 mils (100 $\pm$ 25.4 μ m).
- 3-3 Dual Bonding pad: 7.7 mils x 7.7mils (195 μ m x 195 μ m).
- 3-4 Pattern drawing: Refer to the attached drawing.

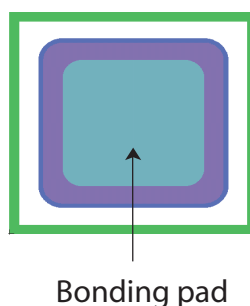
4. Electrical Characteristics (Ta=25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Zener Voltage	V _Z (Top)	I _Z =5mA	5.8	-	7.0	V
	V _Z (Back)		5.4	-	6.6	
Forward Voltage	V _f	I _F =20mA			1.2	V
Reverse Leakage Current	I _R	V _R =4V			100	nA
Electrostatic Discharge	ESD	HBM MIL-STD 883	8.0			KV

5. Drawing:



(Top View)



6. Protection Circuit:

